

REMARKS

Copies of non-patent literature citations Nos. 12, and 14-18, cited and provided in the parent application, are attached. Applicants respectfully request the Examiner to initial and return a copy of the 1449 indicating that the references have been considered.

Support for new claims 21 and 22 can be found at the top of page 4.

Rejection Under 35 U.S.C. §102(b) and 103

The rejections under Ohnishi are respectfully traversed.

Ohnishi (EP 618 612) teaches a cleaning technique used to remove contaminants such as organic residues, inorganic residues, other residues, and particles from a surface of a semiconductor substrate (see column 2, lines 47-56). Ohnishi adds fluorosulfuric acid to sulfuric acid in order to generate HF by the reaction with water molecules which are present in the solution. Hydrogen peroxide is added to achieve a constant etching rate.

Firstly, with regard to new claim 22 (see page 4, top, of the specification), Ohnishi is especially irrelevant because his fluorine-containing compounds contain cations having a valence other than +1. See Col. 2, line 49, col. 3, line 15 and col. 7, line 19, etc., showing that the compound, fluorosulfuric acid, is in equilibrium in solution among various species, including SO_2F_2 , HSO_3F , and HF, not all of which have cations of a valence of +1.

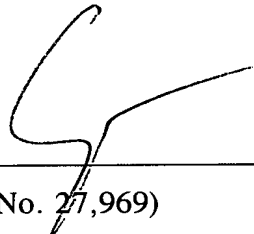
Furthermore, sidewall residue is the result of what happens to photoresist coatings after exposure, developing and etching. Such photoresist sidewall residue can not be removed by simple washing. For instance, a suitable solution must be able to remove the sidewall residue from the narrow deepenings and cavities of the wafer structure without etching or damaging the wafer surface structure. Ohnishi does not describe the removal of such sidewall residue after dry etching. It describes only washing residue from the surface of the substrate. It is another thing entirely to provide a process which effectively removes sidewall residue from such areas as the mentioned difficult to reach narrow deepenings and


cavities. Nothing in Ohnishi suggests contacting sidewall residue in the manner required by the claims.

Thus, the reference fails to teach or suggest a process for removing sidewall residue after drywall etching , as claimed.

The claims of the application are submitted to be in condition for allowance. However, should the examiner have any questions or comments, he is cordially invited to telephone the undersigned at the number below.

Respectfully submitted,



Anthony Zelano (Reg. No. 27,969)
Attorney for Applicants

Jennifer Branigan (Reg. No. 40,921)
Patent Agent

MILLEN, WHITE, ZELANO & BRANIGAN, P.C.
Arlington Courthouse Plaza 1
2200 Clarendon Blvd., Suite 1400
Arlington, Virginia 22201
Telephone: (703) 812-5305
Internet Address: jbranigan@mwzb.com

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